

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	192	438/761.ccls. and (stress\$4 or strain\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:42
L2	182	438/761.ccls. and (stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:43
L3	113	438/761.ccls. and (stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:44
L4	72	438/761.ccls. and (stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:45

L5	2	438/ 761.ccls. and (stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench) and (pit\$2 or dip\$2) same (fill\$4 or cover)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:46
L6	1	257/E21.598,E21.599. ccls. and (stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench) and (pit\$2 or dip\$2) same (fill\$4 or cover)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:48
L7	19	(stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench) and (pit\$2 or dip\$2) same (fill\$4 or cover) and huang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:51

L8	0	(stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench) and (pit\$2 or dip\$2) same (fill\$4 or cover) and huang.asn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:54
L9	0	(stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench) and (pit\$2 or dip\$2) same (fill\$4 or cover) and huang.asn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:55
L10	3238	(stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench) and (pit\$2 or dip\$2) same (fill\$4 or cover)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:55

L11	1591	(stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench) and (pit\$2 or dip\$2) same (fill\$4 or cover) and (dic\$4 or cut \$4) same (substrate or wafer or carrier or base or plate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:57
L12	102	(stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench) and (pit\$2 or dip\$2) same (fill\$4 or cover) and (dic\$4 or cut \$4) same (substrate or wafer or carrier or base or plate) and scribe	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/26 13:58
L13	3	(stress\$4 or strain\$4) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (opening\$4 or via or hole or trench) same (dielectric or oxide or insulat\$4) and (fill\$4 or cover) same (opening \$4 or via or hole or trench) and (pit\$2 or dip\$2) same (fill\$4 or cover) and (dic\$4 or cut \$4) same (substrate or wafer or carrier or base or plate) and	US-PGPUB	OR	ON	2009/03/26 14:06

		scribe.clm.				
S1	5	("6566722") or ("6611037"). PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/06/09 13:46
S2	0	S1 and substrate and well and "conductive type" and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:49
S3	0	S1 and substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:49
S5	0	substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon and "epitaxial silicon" and buffer and photodiode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:50
S6	17	substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon and "epitaxial silicon" and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:51
S7	663	substrate and well and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:52

S8	74	substrate and well and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer and photodiode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:01
S9	53	substrate and well and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer and photodiode and (STI or LOCOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:05
S10	9	substrate and "well region" and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer and photodiode and (STI or LOCOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:06
S11	93	substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:49
S12	4	"6569700"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:53
S13	1171	(trench near9 (well near region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:55
S14	597	(trench near9 (well near region)) near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:55

S15	598	(trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:56
S16	2	(trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer) and (photosensitive near4 area)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:56
S17	11	(trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer) and photosensitive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:15
S18	4	dop\$4 near9 (trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer) and photosensitive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:24
S19	8	dop\$4 near9 (trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer) and (photosensitive or photodiode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:34
S20	65838	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:39
S21	8359	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and well near9 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:40
S22	238	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and (well near9 (substrate or wafer or semiconductor)) and (trench\$2 near9 well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:43

S23	145	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and (well near9 (substrate or wafer or semiconductor)) and (trench\$2 near9 well) and dop\$4 near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:44
S24	23	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and (well near9 (substrate or wafer or semiconductor)) and (trench\$2 near9 well) and (dop\$4 near9 (substrate or semiconductor or wafer)) and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:44
S25	6	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and (well near9 (substrate or wafer or semiconductor)) and (trench\$2 near9 well) and (dop\$4 near9 (substrate or semiconductor or wafer)) and anneal and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:03
S26	9923	(plural\$4 near9 trench \$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:04
S27	321	(plural\$4 near9 trench \$2) near9 well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:04
S28	144	(plural\$4 near9 trench \$2) near9 well near9 (semiconductor or substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 14:21

S29	0	(plural\$4 near9 trench \$2) near9 well near9 (semiconductor or substrate or wafer) and (438/21.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/22 11:44
S30	3	("6611037").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2007/03/21 08:34
S31	0	("(dop\$4nearlayer) near9anneal").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/19 12:14
S32	193	(dop\$4 near layer) near9 anneal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/19 12:15
S33	7	(dop\$4 near layer) near9 anneal and (photodiode or photosensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/19 12:19
S34	6	(dop\$4 near layer) near9 anneal and (photodiode or photosensor) and (polysilicon or (epitaxial near silicon))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/19 12:19
S35	59	(photosensitive or photosensor) and (buffer near9 (polysilicon or (epitaxial near silicon)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 08:36
S36	5	(photosensitive or photosensor) and (buffer near9 (polysilicon or (epitaxial near silicon))) near9 CVD	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 08:38
S37	0	(photosensitive or photosensor) and (buffer near9 (polysilicon or (epitaxial near silicon))) near9 CVD and anneal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 08:38

S38	6	(photosensitive or photosensor) and (buffer near9 (polysilicon or (epitaxial near silicon))) near9 (CVD or "chemical vapor deposition")	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:55
S39	9	(photosensitive or photosensor) and (anneal near9 (dop\$4 near layer))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:56
S40	9	(photosensitive or photosensor or phototransistor) and (anneal near9 (dop\$4 near layer))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 12:19
S41	20	(photosensitive or photosensor or phototransistor) and (anneal near9 (buffer near layer))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 12:20
S42	0	(photosensitive or photosensor or phototransistor) and (anneal near9 (buffer near layer)) and (dop \$4 near layer)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 12:21
S43	17	(photosensitive or photosensor or phototransistor) and (anneal near9 (buffer near layer)) and (dop \$4 near4 layer)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 12:21
S44	17	(photosensitive or photosensor or phototransistor) and (anneal near9 (buffer near (layer or film))) and (dop\$4 near4 (layer or film))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 12:24

S45	0	(photosensitive or photosensor or phototransistor) and (anneal near9 (buffer near (layer or film))) and (dop\$4 near4 (layer or film)) and ((driv\$4 or disperse or abort) near9 dop\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 12:25
S46	0	(photosensitive or photosensor or phototransistor) and (anneal near9 (buffer near (layer or film))) and (dop\$4 near4 (layer or film)) and ((driv\$4 or dispers\$4 or abort or exit or escap\$4) near9 dop\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 12:26
S47	397	photodiode and (substrate or wafer or base) and (well near region) and (isolation near structure) or "STI" and (trench\$2 or via\$4 or hole\$2 or opening\$2 or recess\$2 or aperture\$2) and (dop\$4 near9 well) and photosensitive	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 09:36
S48	131	photodiode and (substrate or wafer or base) and (well near region) and (isolation near structure) or "STI" and (trench\$2 or via\$4 or hole\$2 or opening\$2 or recess\$2 or aperture\$2) and (dop\$4 near9 well) and photosensitive and anneal\$4 and (well near region) near9 (substrate or wafer or base)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 09:36

S49	122	photodiode and (substrate or wafer or base) and (well near region) and (isolation near structure) or "STI" and (trench\$2 or via\$4 or hole\$2 or opening\$2 or recess\$2 or aperture\$2) and (dop\$4 near9 well) and photosensitive and anneal\$4 and (well near region) near9 (substrate or wafer or base) and (buffer or polysilicon or (epitaxial near silicon)) near9 (well near region) and junction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 10:20
S50	122	photodiode and (substrate or wafer or base) and (well near region) and (isolation near structure) or "STI" and (trench\$2 or via\$4 or hole\$2 or opening\$2 or recess\$2 or aperture\$2) and (dop\$4 near9 well) and (photosensitive near area) and anneal\$4 and (well near region) near9 (substrate or wafer or base) and (buffer or polysilicon or (epitaxial near silicon)) near9 (well near region) and junction and cvd	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 10:21
S51	122	photodiode and (substrate or wafer or base) and (well near region) and (isolation near structure) or "STI" and (trench\$2 or via\$4 or hole\$2 or opening\$2 or recess\$2 or aperture\$2) and (dop\$4 near9 well) and (photosensitive near area) and anneal\$4 and (well near region) near9 (substrate or wafer or base) and (buffer or polysilicon or	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 10:22

		(epitaxial near silicon)) near9 (well near region) and junction and cvd and fill near9 (trench\$2 or via\$4 or hole\$2 or opening\$2 or recess\$2 or aperture \$2)				
S52	122	photodiode and (substrate or wafer or base) and (well near region) and (isolation near structure) or "STI" and (trench\$2 or via\$4 or hole\$2 or opening\$2 or recess\$2 or aperture\$2) and (dop\$4 near9 well) and (photosensitive near area) and anneal\$4 and (well near region) near9 (substrate or wafer or base) and (buffer or polysilicon or (epitaxial near silicon)) near9 (well near region) and junction and cvd and fill\$4 near4 (trench\$2 or via \$4 or hole\$2 or opening \$2 or recess\$2 or aperture\$2)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 11:02
S53	147190	(photodiode or photosensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 11:03
S54	1516	(photodiode or photosensor) and (photosensitive near area)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 11:04
S55	12	(photodiode or photosensor) and (photosensitive near area) and (trench or opening or via or recess or aperture or hole) near9 (well near region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 11:08

S56	98	(photodiode or photosensor) and (photosensitive near area) and (trench or opening or via or recess or aperture or hole) near9 (photosensitive near area)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 11:50
S57	11	(photodiode or photosensor) and (photosensitive near area) and (trench or opening or via or recess or aperture or hole) near9 (photosensitive near area) and (deposit\$4 near9 dop\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 11:55
S58	94	(photodiode or photosensor) and (photosensitive near area) and (trench or opening or via or recess or aperture or hole) and (deposit\$4 near9 dop\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 11:59
S59	15	(photodiode or photosensor) and (photosensitive near area) and (deposit\$4 near9 dop\$4) near9 (trench or opening or via or recess or aperture or hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 14:49
S60	1	(photodiode or photosensor) and (photosensitive near area) and (deposit\$4 near9 dop\$4) near9 (trench or opening or via or recess or aperture or hole) and (buffer near9 (trench or opening or via or recess or aperture or hole))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 08:42

S61	14	(photodiode or photosensor) and (photosensitive near area) and (buffer near9 (trench or opening or via or recess or aperture or hole))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 14:51
S62	2416429	"6228750" B1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 08:43
S63	6	"6228750"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 08:43
S64	7	(photodiode or photosensor) and (substrate or wafer or carrier or bae or plate) and (photosensitive near9 (area or region)) and (isolat\$4 or "STI" or "FOX") and (well adj (region or area)) and (trench or via or hole or opening or groove or recess) near9 well and (dop\$4 or impur\$4) near9 (film or layer) and wall	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/14 13:50
S65	3	"6611037".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/14 13:52
S66	155898	(photodiode or photosensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/14 14:11
S67	3869	(photodiode or photosensor) and (dop\$4 or impur\$4) near (layer or film)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/14 14:11

S68	343	(photodiode or photosensor) and (dop \$4 or impur\$4) near (layer or film) and (well adj (region or area))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/14 14:11
S69	135	(photodiode or photosensor) and (dop \$4 or impur\$4) near (layer or film) and (well adj (region or area)) and trench	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/14 14:12
S70	42	(photodiode or photosensor) and (dop \$4 or impur\$4) near (layer or film) and (well adj (region or area)) and trench and photosensitive	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/14 14:12
S71	4	(photodiode or photosensor) and (dop \$4 or impur\$4) near (layer or film) and (well adj (region or area)) and trench and photosensitive .clm.	US-PGPUB	OR	ON	2008/08/14 14:12

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